# 2 Data Sheets

This section presents complete electrical specifications for Teccor's *SIDACtor* solid state overvoltage protection devices.

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Part Number						
Catalog	Symbolized					
P0080SA	P-8A					
P0080SB	P-8B					
P0080SC	P-8C					
P0080SD	P-8D					
P0080SC MC	P-8CM					
P0300SA	P03A					
P0300SB	P03B					
P0300SC	P03C					
P0300SD	P03D					
P0300SC MC	P03CM					
P0640SA	P06A					
P0640SB	P06B					
P0640SC	P06C					
P0640SD	P06D					
P0640SC MC	P06CM					
P0641CA2	P62A					
P0641SA	P61A					
P0641SC	P61C					
P0720SA	P07A					
P0720SB	P07B					
P0720SC	P07C					
P0720SD	P07D					
P0720SC MC	P07CM					
P0721CA2	P72A					
P0721SA	P71A					
P0721SC	P71C					
P0900SA	P09A					
P0900SB	P09B					
P0900SC	P09C					
P0900SD	P09D					
P0900SC MC	P09CM					
P0901CA2	P92A					
P0901SA	P91A					
P0901SC	P91C					
P1100SA	P11A					

# **DO-214AA Package Symbolization**

Part Number							
Catalog	Symbolized						
P1100SB	P11B						
P1100SC	P11C						
P1100SD	P11D						
P1100SC MC	P11CM						
P1101CA2	P02A						
P1101SA	P01A						
P1101SC	P01C						
P1200SA	P12A						
P1200SB	P12B						
P1200SC	P12C						
P1200SD	P12D						
P1200SC MC	P12CM						
P1300SA	P13A						
P1300SB	P13B						
P1300SC	P13C						
P1300SD	P13D						
P1300SC MC	P13CM						
P1500SA	P15A						
P1500SB	P15B						
P1500SC	P15C						
P1500SD	P15D						
P1500SC MC	P15CM						
P1800SA	P18A						
P1800SB	P18B						
P1800SC	P18C						
P1800SD	P18D						
P1800SC MC	P18CM						
P2000SA	P20A						
P2000SB	P20B						
P2000SC	P20C						
P2000SD	P20D						
P2000SC MC	P20CM						
P2300SA	P23A						
P2300SB	P23B						
P2300SC	P23C						

Part Number								
Catalog	Symbolized							
P2300SD	P23D							
P2300SC MC	P23CM							
P2500SA	P25A							
P2500SB	P25B							
P2500SC	P25C							
P2500SD	P25D							
P2500SC MC	P25CM							
P2600SA	P26A							
P2600SB	P26B							
P2600SC	P26C							
P2600SD	P26D							
P2600SC MC	P26CM							
P3002CB	P30B							
P3002SB	P30B							
P3100SA	P31A							
P3100SB	P31B							
P3100SC	P31C							
P3100SD	P31D							
P3100SC MC	P31CM							
P3500SA	P35A							
P3500SB	P35B							
P3500SC	P35C							
P3500SD	P35D							
P3500SC MC	P35CM							
P6002CB	P60B							
B1100CA	B10A							
B1100CC	B10C							
B1160CA	B16A							
B1160CC	B16C							
B1200CA	B12A							
B1200CC	B20C							
B2050CA	B20A							
B2050CC	B20C							

Note: Date code is located below the symbolized part number.

# **SIDACtor Device**



DO-214AA *SIDACtor* solid state protection devices protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

#### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0080S_	6	25	4	5	800	2.2	50	100
P0300S_	25	40	4	5	800	2.2	50	110
P0640S_	58	77	4	5	800	2.2	150	50
P0720S_	65	88	4	5	800	2.2	150	50
P0900S_	75	98	4	5	800	2.2	150	50
P1100S_	90	130	4	5	800	2.2	150	40
P1300S_	120	160	4	5	800	2.2	150	40
P1500S_	140	180	4	5	800	2.2	150	40
P1800S_	170	220	4	5	800	2.2	150	30
P2300S_	190	260	4	5	800	2.2	150	30
P2600S_	220	300	4	5	800	2.2	150	30
P3100S_	275	350	4	5	800	2.2	150	30
P3500S_	320	400	4	5	800	2.2	150	30

\* For individual "SA", "SB", and "SC" surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

-  $I_{\text{PP}}$  is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

V<sub>S</sub> is measured at 100 V/µs.

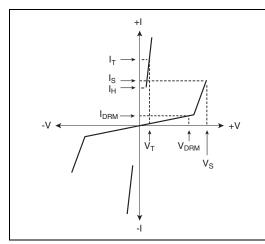
 Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value for "SA" and "SB" product. "SC" capacitance is approximately 2x the listed value. The off-state capacitance of the P0080SB is equal to the "SC" device.

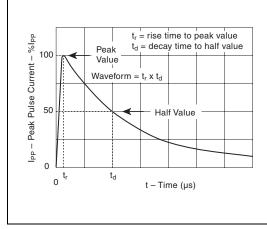
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

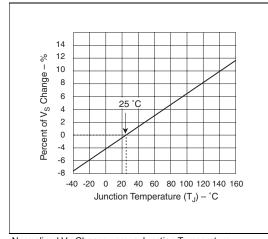
## Thermal Considerations

Package	Symbol	Parameter	Value	Unit
DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	90	°C/W



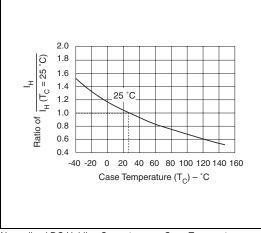


V-I Characteristics



Normalized  $\mathsf{V}_S$  Change versus Junction Temperature





Normalized DC Holding Current versus Case Temperature

# MicroCapacitance (MC) SC SIDACtor Device



The DO-214AA SC MC *SIDACtor* series is intended for applications sensitive to load values. Typically, high speed connections require a lower capacitance.  $C_0$  values for the MicroCapacitance device are 40% lower than a standard SC part.

This MC *SIDACtor* series is used to enable equipment to meet various regulatory requirements including GR 1089, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68). Contact factory regarding ITU K.20, K.21, and K.45.

## **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	Vs Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0080SC MC **	6	25	4	5	800	2.2	50	55
P0300SC MC **	25	40	4	5	800	2.2	50	35
P0640SC MC	58	77	4	5	800	2.2	150	60
P0720SC MC	65	88	4	5	800	2.2	150	60
P0900SC MC	75	98	4	5	800	2.2	150	60
P1100SC MC	90	130	4	5	800	2.2	150	50
P1300SC MC	120	160	4	5	800	2.2	150	50
P1500SC MC	140	180	4	5	800	2.2	150	50
P1800SC MC	170	220	4	5	800	2.2	150	40
P2300SC MC	190	260	4	5	800	2.2	150	40
P2600SC MC	220	300	4	5	800	2.2	150	40
P3100SC MC	275	350	4	5	800	2.2	150	40
P3500SC MC	320	400	4	5	800	2.2	150	40

\* For surge ratings, see table below.

\*\* Contact factory for release date.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

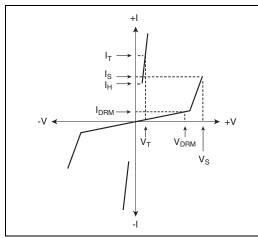
V<sub>S</sub> is measured at 100 V/µs.

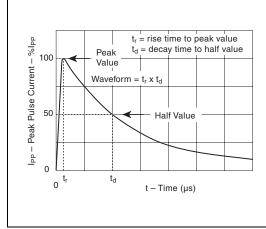
- Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

· Off-state capacitance is measured at 1 MHz with a 2 V bias.

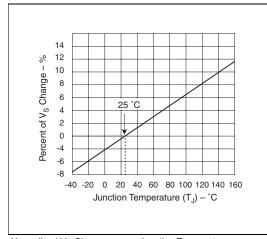
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>ΡΡ</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
С	500	400	200	150	100	50	500

Package	Symbol	Parameter	Value	Unit
DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
	T <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
	R <sub>θJA</sub>	Thermal Resistance: Junction to Ambient	90	°C/W

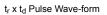


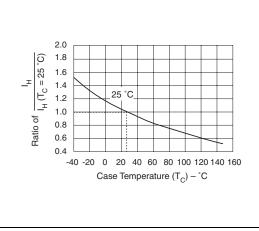


V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature





Normalized DC Holding Current versus Case Temperature

# MicroCapacitance (MC) SA SIDACtor Device



The DO-214AA SA MC *SIDACtor* series is intended for applications sensitive to load values. Typically, high speed connections require a lower capacitance.  $C_0$  values for the MicroCapacitance device are 40% lower than a standard SA part.

This MC *SIDACtor* series is used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA/ EIA-IS-968 (formerly known as FCC Part 68).

## **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0080SA MC	6	25	4	5	800	2.2	50	45
P0300SA MC	25	40	4	5	800	2.2	50	25

\* For surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

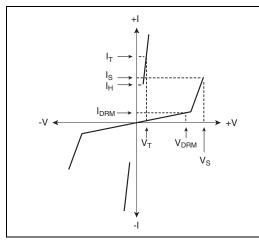
+  $V_S$  is measured at 100 V/µs.

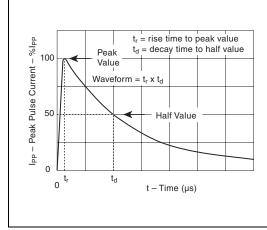
Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

• Off-state capacitance is measured at 1 MHz with a 2 V bias.

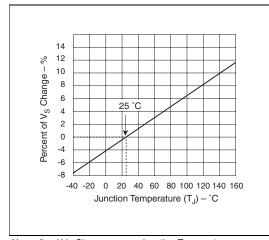
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500

Package	Symbol	Parameter	Value	Unit
DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
	TS	Storage Temperature Range	-65 to +150	°C
	R <sub>θJA</sub>	Thermal Resistance: Junction to Ambient	90	°C/W



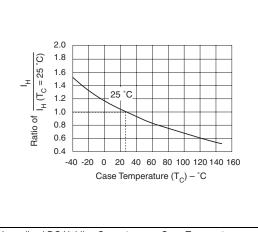


V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature





Normalized DC Holding Current versus Case Temperature

# High Surge Current (D-rated) SIDACtor Device



DO-214AA *SIDACtor* solid state protection devices with a D surge rating protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

These *SIDACtor* devices withstand simultaneous surges incurred in GR 1089 lightning tests. (See "First Level Lightning Surge Test" on page 4-5.) Surge ratings are twice that of a device with a C surge rating. This allows a discrete surface mount version of Teccor's patented "Y" configuration. (US Patent 4,905,119)

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

# **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	Ι <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0080SD **	6	25	4	5	800	2.2	50	200
P0300SD **	25	40	4	5	800	2.2	50	220
P0640SD **	58	77	4	5	800	2.2	50	100
P0720SD **	65	88	4	5	800	2.2	50	100
P0900SD **	75	98	4	5	800	2.2	50	100
P1100SD	90	130	4	5	800	2.2	50	80
P1300SD	120	160	4	5	800	2.2	50	80
P1500SD	140	180	4	5	800	2.2	50	80
P1800SD	170	220	4	5	800	2.2	50	60
P2300SD	190	260	4	5	800	2.2	50	60
P2600SD	220	300	4	5	800	2.2	50	60
P3100SD	275	350	4	5	800	2.2	50	60
P3500SD	320	400	4	5	800	2.2	50	60

\* For surge ratings, see table below.

\*\* Contact factory for release date.

General Notes:

All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

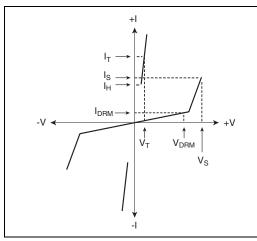
• V<sub>S</sub> is measured at 100 V/µs.

• Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

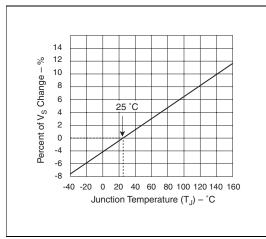
· Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value.

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>ΡΡ</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
D	1000	800	400	300	200	50	1000

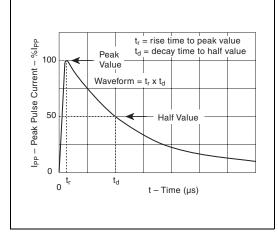
Package	Symbol	Parameter	Value	Unit
DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	90	°C/W



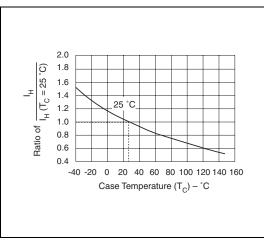
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature



t<sub>r</sub> x t<sub>d</sub> Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

# **Compak Two-chip SIDACtor Device**



The modified DO-214AA SIDACtor device provides low-cost, longitudinal protection.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

# **Electrical Parameters**

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	VT	I <sub>DRM</sub>	Is	Ιτ	Ін	C <sub>O</sub> pF
Number	Pins1	-2, 2-3	Pins	s 1-3	3 Volts		mAmps	Amps	mAmps	Pins 1-3
P3002CA	140	180	280	360	4	5	800	1	120	15
P6002CA	275	350	550	700	4	5	800	1	120	15

\* For surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

•  $V_S$  is measured at 100 V/µs.

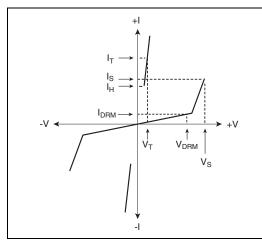
· Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

• Off-state capacitance is measured between Pins 1-3 at 1 MHz with a 2 V bias.

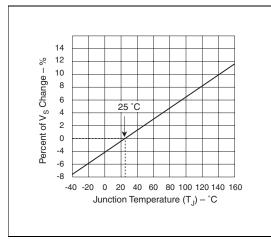
• UL 60950 creepage requirements must be considered.

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500

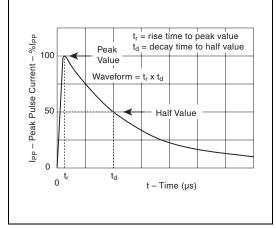
Package	Symbol	Parameter	Value	Unit
Modified DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
Pin 3	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
Pin 1 Pin 2	R <sub>θJA</sub>	Thermal Resistance: Junction to Ambient	85	°C/W



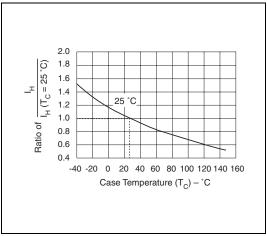
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature



t<sub>r</sub> x t<sub>d</sub> Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

# Ethernet/10BaseT/100BaseT Protector



The DO-214AA *SIDACtor* Ethernet protection series is intended for applications sensitive to load values. Typically, high speed connections require a lower capacitance.  $C_0$  values are 40% lower than standard devices.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

# **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0642S_	58	77	4	5	800	2.2	150	25
P0722S_	65	88	4	5	800	2.2	150	25
P0902S_	75	98	4	5	800	2.2	150	25
P1102S_	90	130	4	5	800	2.2	150	20
P3002S_	280	360	4	5	800	2.2	150	15

\* For surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• I<sub>PP</sub> is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

• V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

V<sub>S</sub> is measured at 100 V/µs.

Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

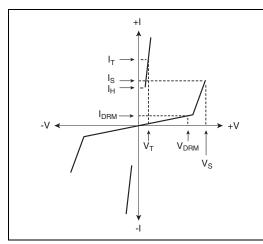
Off-state capacitance is measured at 1 MHz with a 2 V bias.

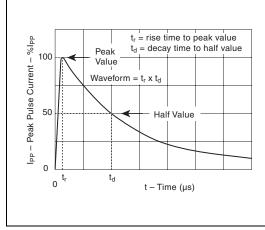
# Surge Ratings

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
Α	150	150	90	50	45	20	500
B**	250	250	150	100	80	30	500

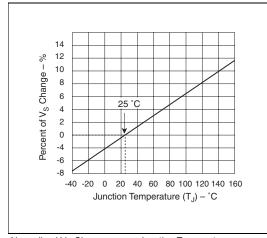
\*\* Contact factory for release date of B-rated devices.

Package	Symbol	Parameter	Value	Unit
DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
	T <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	90	°C/W



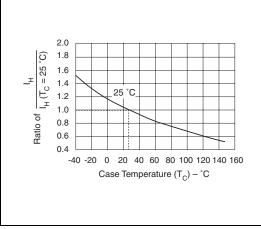


V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature

t<sub>r</sub> x t<sub>d</sub> Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

# **SIDACtor Device**



TO-92 *SIDACtor* solid state protection devices protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68)

## **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0080E_	6	25	4	5	800	2.2	50	100
P0300E_	25	40	4	5	800	2.2	50	110
P0640E_	58	77	4	5	800	2.2	150	50
P0720E_	65	88	4	5	800	2.2	150	50
P0900E_	75	98	4	5	800	2.2	150	50
P1100E_	90	130	4	5	800	2.2	150	40
P1300E_	120	160	4	5	800	2.2	150	40
P1500E_	140	180	4	5	800	2.2	150	40
P1800E_	170	220	4	5	800	2.2	150	30
P2300E_	190	260	4	5	800	2.2	150	30
P2600E_	220	300	4	5	800	2.2	150	30
P3100E_	275	350	4	5	800	2.2	150	30
P3500E_	320	400	4	5	800	2.2	150	30

\* For individual "EA", "EB", and "EC" surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

-  $I_{\text{PP}}$  is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

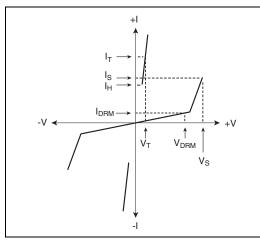
V<sub>S</sub> is measured at 100 V/µs.

• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value for "EA" and "EB" product. "EC" capacitance is approximately 2x the listed value. The off-state capacitance of the P0080EB is equal to the "EC" device.

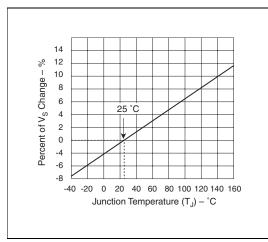
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	10x560 µs 10x1000 µs		di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

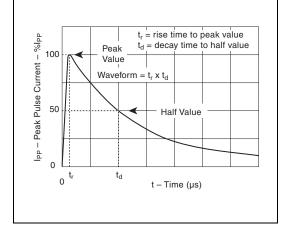
Package	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature Range	-40 to +150	°C
TO-92	TS	Storage Temperature Range	-65 to +150	°C
	R <sub>θJA</sub>	Thermal Resistance: Junction to Ambient	90	°C/W



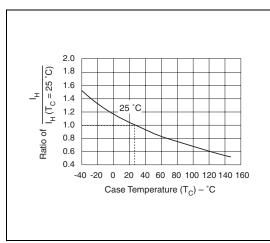
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature



tr x td Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

# MicroCapacitance (MC) SIDACtor Device



The TO-92 MC *SIDACtor* series is intended for applications sensitive to load values. Typically, high speed connections require a lower capacitance.  $C_0$  values for MC devices are 40% lower than a standard EC part.

This MC *SIDACtor* series is used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA/ EIA-IS-968 (formerly known as FCC Part 68) without the need of series resistors.

## **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> µAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0640EC MC	58	77	4	5	800	2.2	150	60
P1500EC MC	140	180	4	5	800	2.2	150	50
P2600EC MC	220	300	4	5	800	2.2	150	40
P3100EC MC	275	350	4	5	800	2.2	150	40

\* For surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

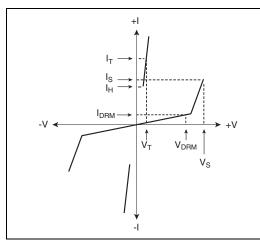
V<sub>S</sub> is measured at 100 V/µs.

· Special voltage (Vs and VDRM) and holding current (IH) requirements are available upon request.

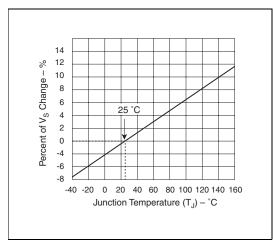
• Off-state capacitance is measured at 1 MHz with a 2 V bias.

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	I <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
С	500	400	200	150	100	50	500

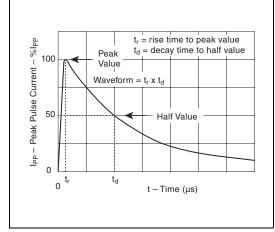
Package	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature Range	-40 to +150	°C
TO-92	T <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
	R <sub>θJA</sub>	Thermal Resistance: Junction to Ambient	90	°C/W



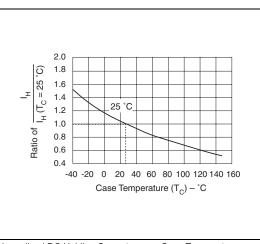
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature







Normalized DC Holding Current versus Case Temperature

# **Balanced Three-chip SIDACtor Device**



This balanced protector is a surface mount alternative to the modified TO-220 package. Based on a six-pin surface mount SOIC package, it uses Teccor's patented "Y" (US Patent 4,905,119) configuration. It is available in surge current ratings up to 500 A.

SIDACtor devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

## **Electrical Parameters**

Part	VDRM VS VDRM VS   Volts Volts Volts Volts V		Ірри	Is	Гт	Iн	с <sub>о</sub>			
Number *	Pins 1	-3, 1-4	Pins	s 3-4	Volts	μAmps	mAmps	Amps	mAmps	pF
P1553U_	130	180	130	180	8	5	800	2.2	150	40
P1803U_	150	210	150	210	8	5	800	2.2	150	40
P2103U_	170	250	170	250	8	5	800	2.2	150	40
P2353U_	200	270	200	270	8	5	800	2.2	150	40
P2703U_	230	300	230	300	8	5	800	2.2	150	30
P3203U_	270	350	270	350	8	5	800	2.2	150	30
P3403U_	300	400	300	400	8	5	800	2.2	150	30
P5103U_	420	600	420	600	8	5	800	2.2	150	30
A2106U_ **	170	250	50	80	8	5	800	2.2	120	40
A5030U_ **	400	550	270	350	8	5	800	2.2	150	30

\* For individual "UA", "UB", and "UC" surge ratings, see table below. \*\* Asymmetrical

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

• Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

V<sub>S</sub> is measured at 100 V/µs.

• Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

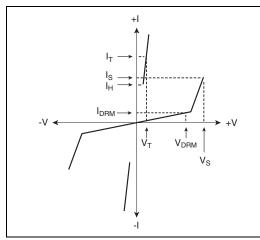
Off-state capacitance is measured between Pins 1-3 and 1-4 at 1 MHz with a 2 V bias and is a typical value for "UA" product. "UB" and "UC" capacitance is approximately 2x higher.

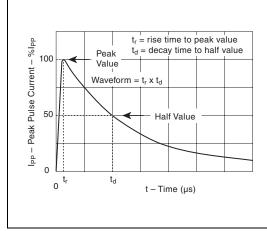
· Device is designed to meet balance requirements of GTS 8700 and GR 974.

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

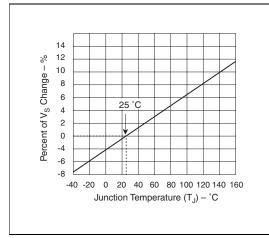
#### Thermal Considerations

Package	Symbol	Parameter	Value	Unit
Modified MS-013	TJ	Operating Junction Temperature Range	-40 to +125	°C
6 5	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
1 2 3 4 4	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W

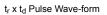


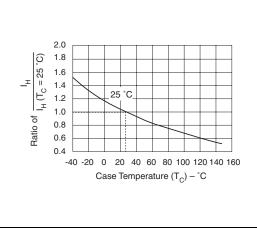


V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature





# Normalized DC Holding Current versus Case Temperature

# **Multiport SIDACtor Device**



The multiport line protector is an integrated multichip solution for protecting multiple twisted pair from overvoltage conditions. Based on a six-pin surface mount SOIC package, it is equivalent to four discrete DO-214AA or two TO-220 packages. Available in surge current ratings up to 500 A, the multiport line protector is ideal for densely populated, high-speed line cards that cannot afford PCB inefficiencies or the use of series power resistors.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

# **Electrical Parameters**

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	VT	IDRM	ls	Іт	Ін	Co
Number *	Pins 1-2, 3	-2, 4-5, 6-5	Pins 1	-3, 4-6	Volts	μAmps	mAmps	Amps	mAmps	pF
P0084U_	6	25	12	50	4	5	800	2.2	50	100
P0304U_	25	40	50	80	4	5	800	2.2	50	110
P0644U_	58	77	116	154	4	5	800	2.2	150	50
P0724U_	65	88	130	176	4	5	800	2.2	150	50
P0904U_	75	98	150	196	4	5	800	2.2	150	50
P1104U_	90	130	180	260	4	5	800	2.2	150	40
P1304U_	120	160	240	320	4	5	800	2.2	150	40
P1504U_	140	180	280	360	4	5	800	2.2	150	40
P1804U_	170	220	340	440	4	5	800	2.2	150	30
P2304U_	190	260	380	520	4	5	800	2.2	150	30
P2604U_	220	300	440	600	4	5	800	2.2	150	30
P3104U_	275	350	550	700	4	5	800	2.2	150	30
P3504U_	320	400	640	800	4	5	800	2.2	150	30

\* For individual "UA", "UB", and "UC" surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

+  $V_{DRM}$  is measured at  $I_{DRM},$  and  $V_S$  is measured at 100 V/µs.

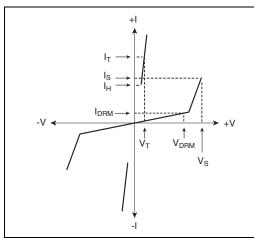
Off-state capacitance is measured between Pins 1-2 and 3-2 at 1 MHz with a 2 V bias and is a typical value for "UA" product. "UB" and "UC" capacitance is approximately 2x higher.

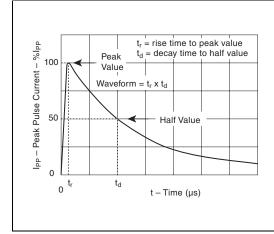
## Surge Ratings

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
Α	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

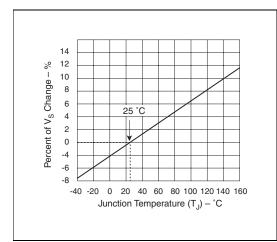
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Package	Symbol	Parameter	Value	Unit
Modified MS-013	ТJ	Operating Junction Temperature Range	-40 to +150	°C
6 5	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
1 2 3	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W

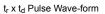


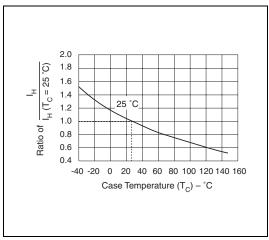


V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature





Normalized DC Holding Current versus Case Temperature

# **Multiport Balanced SIDACtor Device**



This multiport balanced protector is a surface mount alternative to the modified TO-220 package. It is based on a six-pin surface mount SOIC package and uses Teccor's patented "Y" (US Patent 4,905,119) configuration. It is available in surge current ratings up to 500 A.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volt	V <sub>S</sub> Volts	VT	IDRM	ls	Іт	Ін	C <sub>O</sub> pF
Number *	Pins 1-2	, 2-3, 1-3	Pins 4-5	, 5-6, 4-6	Volts	μAmps	mAmps	Amps	mAmps	Pins 3-2, 6-5, 1-2, 4-5
P1556U_	130	180	130	180	8	5	800	2.2	150	50
P1806U_	150	210	150	210	8	5	800	2.2	150	50
P2106U_	170	250	170	250	8	5	800	2.2	150	40
P2356U_	200	270	200	270	8	5	800	2.2	150	40
P2706U_	230	300	230	300	8	5	800	2.2	150	40
P3206U_	270	350	270	350	8	5	800	2.2	150	40
P3406U_	300	400	300	400	8	5	800	2.2	150	40
P5106U_	420	600	420	600	8	5	800	2.2	150	40

# **Electrical Parameters — Symmetrical**

# **Electrical Parameters — Asymmetrical**

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volt	V <sub>S</sub> Volts	VT	I <sub>DRM</sub>	Is	Гт	IH	Co
Number *	Pins 1	-2, 2-3	Pins 4	-6, 1-3	Volts	μAmps	mAmps	Amps	mAmps	pĔ
A2106U_6	170	250	50	80	3.5	5	800	2.2	120	40
A5030U_6	400	550	270	350	3.5	5	800	2.2	150	30

\* For individual "UA", "UB", and "UC" surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. I<sub>PP</sub> applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

+  $V_S$  is measured at 100 V/µs.

• Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

Off-state capacitance is measured between Pins 1-2 and 3-2 at 1 MHz with a 2 V bias and is a typical value for "UA" product. "UB" and "UC" capacitance is approximately 10 pF higher.

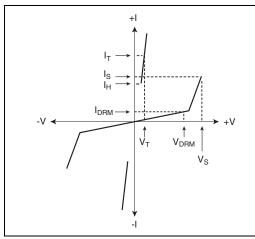
• Device is designed to meet balance requirements of GTS 8700 and GR 974.

#### Surge Ratings

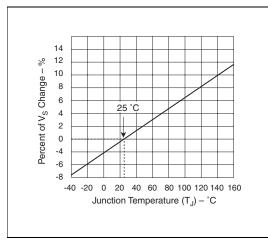
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

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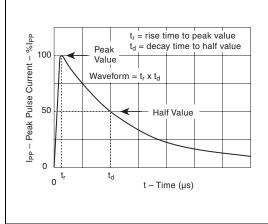
Package	Symbol	Parameter	Value	Unit
Modified MS-013	TJ	Operating Junction Temperature Range	-40 to +125	°C
6	TS	Storage Temperature Range	-65 to +150	°C
1 2 3 4	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W

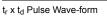


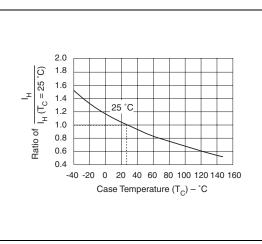
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature







Normalized DC Holding Current versus Case Temperature

# **SIDACtor Device**



The modified TO-220 Type 61 *SIDACtor* solid state protection device can be used in telecommunication protection applications that do not reference earth ground.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

## **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	Ι <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P2000AA61	180	220	4	5	800	2.2	150	30
P2200AA61	200	240	4	5	800	2.2	150	30
P2400AA61	220	260	4	5	800	2.2	150	30
P2500AA61	240	290	4	5	800	2.2	150	30
P3000AA61	270	330	4	5	800	2.2	150	30
P3300AA61	300	360	4	5	800	2.2	150	30

\* For surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

• Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

• V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

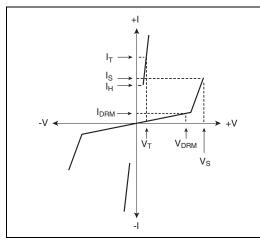
•  $V_S$  is measured at 100 V/µs.

• Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

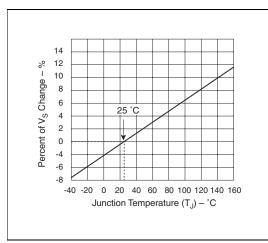
• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value.

Series	l <sub>PP</sub> 0.2x310 μs Amps	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 5x320 μs Amps	I <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	20	150	150	90	50	75	45	20	500

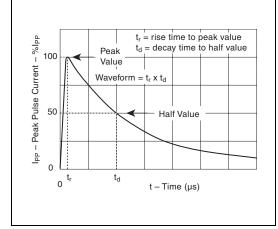
Package	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature Range	-40 to +150	°C
Modified TO-220	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
Type 61	$R_{\theta JA}$	Thermal Resistance: Junction to Ambient	50	°C/W



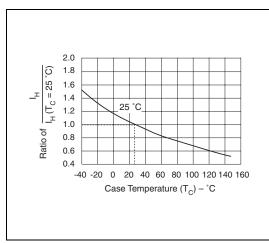
V-I Characteristics



Normalized  $\mathsf{V}_\mathsf{S}$  Change versus Junction Temperature



tr x td Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

# **Two-chip SIDACtor Device**



The two-chip modified TO-220 *SIDACtor* solid state device protects telecommunication equipment in applications that reference Tip and Ring to earth ground but do not require balanced protection.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

## **Electrical Parameters**

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	VT	I <sub>DRM</sub>	Is	г	Iн	co
Number *	Pins 1-2	, 3-2	Pins	s 1-3	Volts	μAmps	mAmps	Amps	mAmps	pF
P0602A_	25	40	50	80	4	5	800	2.2	50	110
P1402A_	58	77	116	154	4	5	800	2.2	150	50
P1602A_	65	95	130	190	4	5	800	2.2	150	50
P2202A_	90	130	180	260	4	5	800	2.2	150	40
P2702A_	120	160	240	320	4	5	800	2.2	150	40
P3002A_	140	180	280	360	4	5	800	2.2	150	40
P3602A_	170	220	340	440	4	5	800	2.2	150	40
P4202A_	190	250	380	500	4	5	800	2.2	150	30
P4802A_	220	300	440	600	4	5	800	2.2	150	30
P6002A_	275	350	550	700	4	5	800	2.2	150	30

\* For individual "AA", "AB", and "AC" surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

• Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

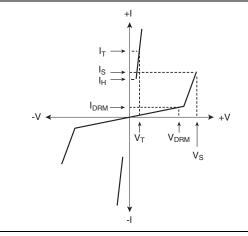
V<sub>S</sub> is measured at 100 V/µs.

• Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

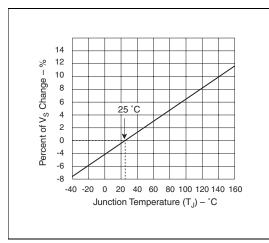
• Off-state capacitance is measured between Pins 1-2 and 3-2 at 1 MHz with a 2 V bias and is a typical value for "AA" and "AB" product. "AC" capacitance is approximately 2x the listed value.

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

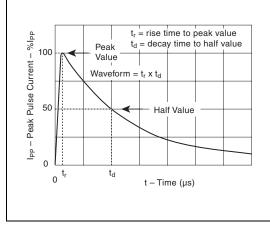
Pack	age	Symbol	Parameter	Value	Unit
		TJ	Operating Junction Temperature Range	-40 to +150	°C
Modified TO-220	$\sim$	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
	IN 1 PIN 2	$R_{0JA}$	Thermal Resistance: Junction to Ambient	50	°C/W



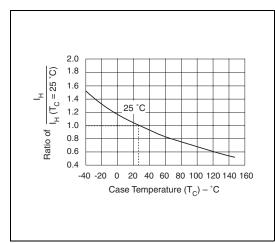
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature



 $t_r \ x \ t_d$  Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

# Two-chip MicroCapacitance (MC) SIDACtor Device



The two-chip modified TO-220 MC *SIDACtor* solid state device protects telecommunication equipment in applications that reference Tip and Ring to earth ground but do not require balanced protection.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

# **Electrical Parameters**

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	VT	IDRM	Is	г	Iн	co
Number *	Pins 1-2,	3-2	Pins	s 1-3	Volts	μAmps	mAmps	Amps	mAmps	pF
P0602AC MC	25	40	50	80	4	5	800	2.2	50	60
P1402AC MC	58	77	116	154	4	5	800	2.2	150	60
P1602AC MC	65	95	130	190	4	5	800	2.2	150	60
P2202AC MC	90	130	180	260	4	5	800	2.2	150	50
P2702AC MC	120	160	240	320	4	5	800	2.2	150	50
P3002AC MC	140	180	280	360	4	5	800	2.2	150	50
P3602AC MC	170	220	340	440	4	5	800	2.2	150	40
P4202AC MC	190	250	380	500	4	5	800	2.2	150	40
P4802AC MC	220	300	440	600	4	5	800	2.2	150	40
P6002AC MC	275	350	550	700	4	5	800	2.2	150	40

\* For surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

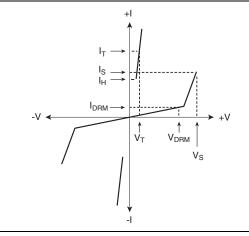
V<sub>S</sub> is measured at 100 V/µs.

Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

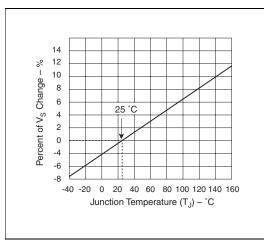
• Off-state capacitance is measured between Pins 1-2 and 3-2 at 1 MHz with a 2 V bias.

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
С	500	400	200	150	100	50	500

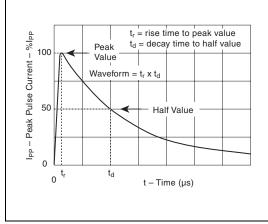
Package	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature Range	-40 to +150	°C
Modified TO-220	TS	Storage Temperature Range	-65 to +150	°C
PIN 1 PIN 2	R <sub>0JA</sub>	Thermal Resistance: Junction to Ambient	50	°C/W



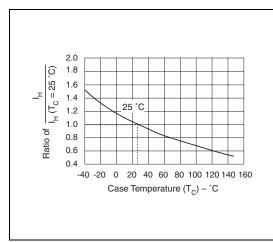
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature



 $t_r \ x \ t_d$  Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

# **Balanced Three-chip SIDACtor Device**



The three-chip modified TO-220 *SIDACtor* balanced solid state device is designed for telecommunication protection systems that reference Tip and Ring to earth ground. Applications include any piece of transmission equipment that requires balanced protection. This device is built using Teccor's patented "Y" (US Patent 4,905,119) configuration.

The *SIDACtor* device is used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20,K.21 and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68).

# **Electrical Parameters**

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	VT	IDRM	ls	Iт	Ін	Co	
Number *	Pins 1	-2, 2-3	Pins 1-3		Volts	μAmps	mAmps	Amps	mAmps	pF	
P1553A_	130	180	130	180	8	5	800	2.2	150	40	
P1803A_	150	210	150	210	8	5	800	2.2	150	40	
P2103A_	170	250	170	250	8	5	800	2.2	150	40	
P2353A_	200	270	200	270	8	5	800	2.2	150	40	
P2703A_	230	300	230	300	8	5	800	2.2	150	30	
P3203A_	270	350	270	350	8	5	800	2.2	150	30	
P3403A_	300	400	300	400	8	5	800	2.2	150	30	
P5103A_	420	600	420	600	8	5	800	2.2	150	30	
A2106A_**	170	250	50	80	8	5	800	2.2	120	40	
A5030A_ **	400	550	270	350	8	5	800	2.2	150	30	

\* For individual "AA", "AB", and "AC" surge ratings, see table below.

\*\* Asymmetrical

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

• V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

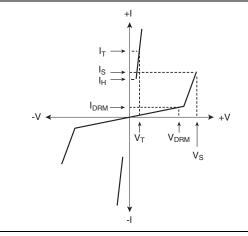
V<sub>S</sub> is measured at 100 V/µs.

- · Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.
- Off-state capacitance is measured between Pins 1-2 and 3-2 at 1 MHz with a 2 V bias and is a typical value for "AA" product. "AB" and "AC" capacitance is approximately 2x the listed value.

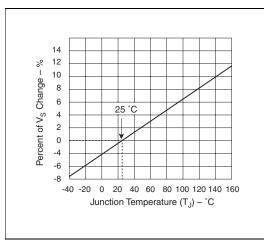
· Device is designed to meet balance requirements of GTS 8700 and GR 974.

Series	l <sub>PP</sub> 2x10 μs Amps	I <sub>PP</sub> 8x20 µs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

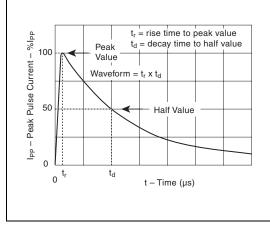
Package	Symbol	Parameter	Value	Unit	
	TJ	Operating Junction Temperature Range	-40 to +150	°C	
Modified TO-220	T <sub>S</sub>	Storage Temperature Range	-65 to +150	°C	
PIN 1 PIN 2 PIN 2	R <sub>0JA</sub>	Thermal Resistance: Junction to Ambient	50	°C/W	

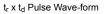


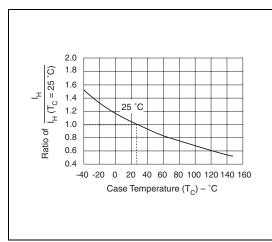
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature







Normalized DC Holding Current versus Case Temperature

# Balanced Three-chip MicroCapacitance (MC) SIDACtor Device



The balanced three-chip TO-220 MC *SIDACtor* solid state device protects telecommunication equipment in high-speed applications that are sensitive to load values and that require a lower capacitance.  $C_0$  values for the MC are 40% lower than a standard AC part.

This MC *SIDACtor* series is used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA/EIA-IS-968 (formerly known as FCC Part 68) without the need of series resistors.

## **Electrical Parameters**

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	VT	I <sub>DRM</sub>	Is	Гт	Iн	co
Number *	Pins 1-2, 2-3		Pins 1-3		Volts	μAmps	mAmps	Amps	mAmps	pF
P1553AC MC	130	180	130	180	8	5	800	2.2	150	40
P1803AC MC	150	210	150	210	8	5	800	2.2	150	40
P2103AC MC	170	250	170	250	8	5	800	2.2	150	40
P2353AC MC	200	270	200	270	8	5	800	2.2	150	40
P2703AC MC	230	300	230	300	8	5	800	2.2	150	30
P3203AC MC	270	350	270	350	8	5	800	2.2	150	30
P3403AC MC	300	400	300	400	8	5	800	2.2	150	30
P5103AC MC	420	600	420	600	8	5	800	2.2	150	30

\* For surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

V<sub>S</sub> is measured at 100 V/µs.

Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

- · Off-state capacitance is measured between Pins 1-2 and 3-2 at 1 MHz with a 2 V bias.
- · Device is designed to meet balance requirements of GTS 8700 and GR 974.

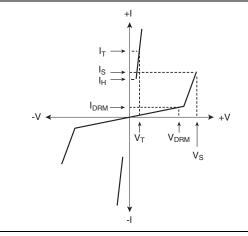
#### Surge Ratings

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
С	500	400	200	150	100	50	500

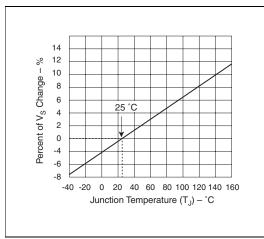
© 2002 Teccor Electronics SIDACtor<sup>®</sup> Data Book and Design Guide

## **Thermal Considerations**

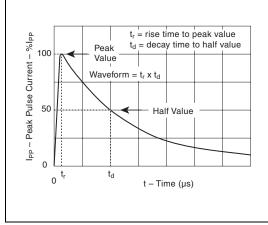
Package	Symbol	Parameter	Value	Unit	
	TJ	Operating Junction Temperature Range	-40 to +150	°C	
Modified TO-220	TS	Storage Temperature Range	-65 to +150	°C	
PIN 1 PIN 2 PIN	R <sub>0JA</sub>	Thermal Resistance: Junction to Ambient	50	°C/W	



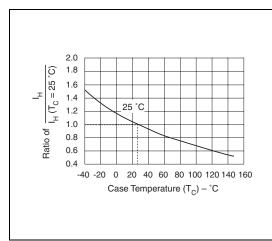
V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature



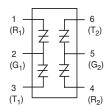
 $t_r \ x \ t_d$  Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

**Data Sheets** 

# **LCAS Asymmetrical Multiport Device**



This is an integrated multichip solution for protecting multiple twisted pair from overvoltage conditions. Based on a six-pin surface mount SOIC package, it is equivalent to four discrete DO-214AA or two TO-220 packages. Available in surge current ratings up to 500 A, the multiport line protector is ideal for densely populated line cards that cannot afford PCB inefficiencies or the use of series power resistors.

For a diagram of an LCAS (Line Circuit Access Switch) application, see Figure 3.21.

## **Electrical Parameters**

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	Vт	IDRM	ls	Ь	IH	С <sub>О</sub> pF
Number *	Pins 3-2, 6-5		Pins 1-2, 4-5		Volts	μAmps	mAmps	Amps	mAmps	Pins 3-2, 6-5, 1-2, 4-5
A1220U_4	100	130	180	220	4	5	800	2.2	120	30
A1225U_4	100	130	230	290	4	5	800	2.2	120	30

\* For individual "UA", "UB", and "UC" surge ratings, see table below.

General Notes:

- All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.
- $I_{\mbox{\scriptsize PP}}$  is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

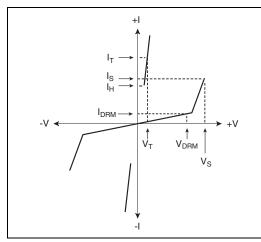
V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

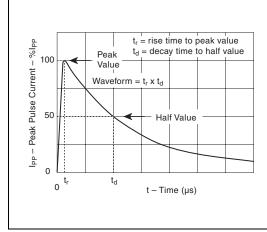
V<sub>S</sub> is measured at 100 V/µs.

- · Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.
- Off-state capacitance is measured between Pins 1-2 and 3-2 at 1 MHz with a 2 V bias and is a typical value for "UA" product. "UB" and "UC" capacitance is approximately 2x higher.

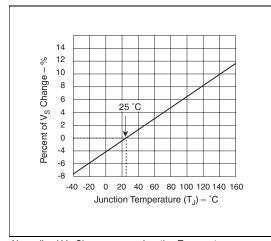
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>ΡΡ</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

Package	Symbol	Parameter	Value	Unit
Modified MS-013	TJ	Operating Junction Temperature Range	-40 to +125	°C
6 5	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
1 2 3	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W



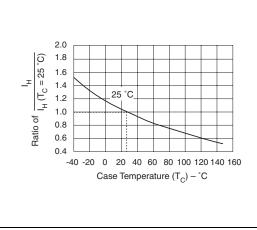


V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature





Normalized DC Holding Current versus Case Temperature

# **LCAS Asymmetrical Discrete Device**



These DO-214AA *SIDACtor* devices are intended for LCAS (Line Circuit Access Switch) applications that require asymmetrical protection in discrete (individual) packages. They enable the protected equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, K.45, IEG 60950, UL 60950, and TIA/EIA-IS-968.

### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> µAmps	l <sub>S</sub> mAmps	l <sub>T</sub> Amps	l <sub>H</sub> mAmps	C <sub>O</sub> pF
P1200S_	100	130	4	5	800	2.2	120	40
P2000S_	180	220	4	5	800	2.2	120	30
P2500S_	230	290	4	5	800	2.2	120	30

\* For individual "SA", "SB", and "SC" surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

• V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

+  $V_{S}$  is measured at 100 V/µs.

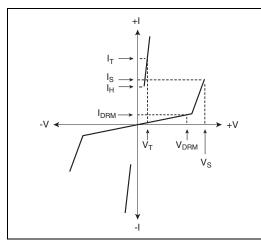
• Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

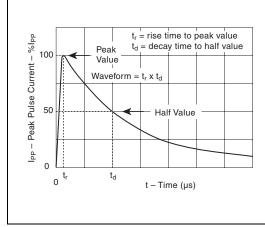
Off-state capacitance is measured between Pins 1-2 and 3-2 at 1 MHz with a 2 V bias and is a typical value for "SA" and "SB" product. "SC" capacitance is approximately 10 pF higher.

Surge Ratings

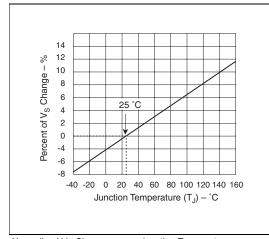
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

Package	Symbol	Parameter	Value	Unit
DO-214AA	TJ	Operating Junction Temperature Range	-40 to +125	°C
	TS	Storage Temperature Range	-65 to +150	°C
	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W

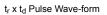


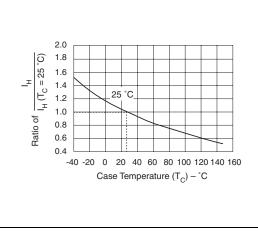


V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature

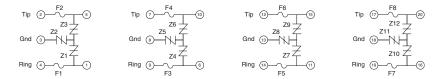




Normalized DC Holding Current versus Case Temperature

# **Four-Port Balanced Three-chip Protector**

This hybrid Single In-line Package (SIP) protects four twisted pairs from overcurrent and overvoltage conditions. Comprised of twelve discrete DO-214AA *SIDACtor* devices and eight *TeleLink* surface mount fuses, it is ideal for densely populated line cards that cannot afford PCB inefficiencies or the use of series power resistors. Surge current ratings up to 500 A are available.



#### **Electrical Parameters**

	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts						C <sub>O</sub> pF
Part Number *	Pins 2-3, 4 12-13, 14-13,	-3, 7-8, 9-8, 17-18, 19-18	Pins 2-4, 7-9, 12-14, 17-19		V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	l <sub>T</sub> Amps	I <sub>H</sub> mAmps	Pins 1-3
P1553Z_	130	180	130	180	8	5	800	2.2	150	40
P1803Z_	150	210	150	210	8	5	800	2.2	150	40
P2103Z_	170	250	170	250	8	5	800	2.2	150	40
P2353Z_	200	270	200	270	8	5	800	2.2	150	40
P2703Z_	230	300	230	300	8	5	800	2.2	150	30
P3203Z_	270	350	270	350	8	5	800	2.2	150	30
P3403Z_	300	400	300	400	8	5	800	2.2	150	30
A2106Z_**	170	250	50	80	8	5	800	2.2	120	40
A5030Z_**	400	550	270	350	8	5	800	2.2	150	30

\* For individual "ZA," "ZB," and "ZC" surge ratings, see table below.

\*\* Asymmetrical General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

V<sub>S</sub> is measured at 100 V/µs.

· Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

• Off-state capacitance is measured between Pins 4-3 and Pins 2-3 at 1 MHz with a 2 V bias and is a typical value for "ZA" product. "ZB" and "ZC" capacitance is approximately 10 pF higher.

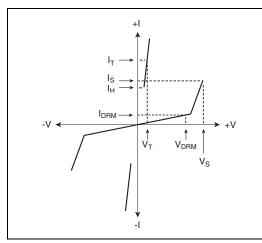
· Device is designed to meet balance requirements of GTS 8700 and GR 974.

### Surge Ratings

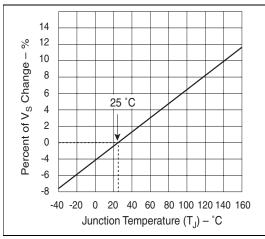
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
Α	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

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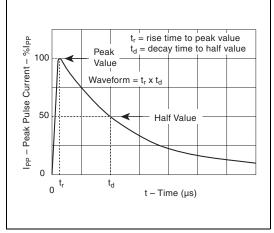
Package	Symbol	Parameter	Value	Unit
SIP	TJ	Operating Junction Temperature Range	-40 to +150	°C
	Ts	Storage Temperature Range	-65 to +150	°C
	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	90	°C/W

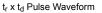


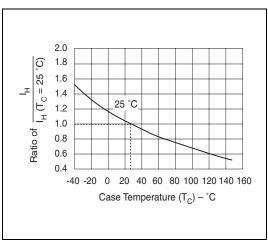
V-I Characteristics







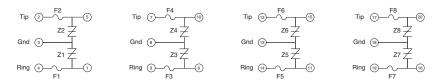




Normalized DC Holding Current versus Case Temperature

# **Four-Port Longitudinal Two-chip Protector**

This hybrid Single In-line Package (SIP) protects four twisted pairs from overcurrent and overvoltage conditions. Comprised of eight discrete DO-214AA *SIDACtor* devices and eight *TeleLink* surface mount fuses, it is ideal for densely populated line cards that cannot afford PCB inefficiencies or the use of series power resistors. Surge current ratings up to 500 A are available.



### **Electrical Parameters**

	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts						Co pF
Part Number *		-3, 7-8, 9-8, 17-18, 19-18	Pins 2 12-14,	-4, 7-9, 17-19	V <sub>T</sub> Volts	Ι <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	Pins 2-3, 3-4
P0602Z_	25	40	50	80	4	5	800	2.2	50	110
P1402Z_	58	77	116	154	4	5	800	2.2	150	50
P1602Z_	65	95	130	190	4	5	800	2.2	150	50
P2202Z_	90	130	180	260	4	5	800	2.2	150	40
P2702Z_	120	160	240	320	4	5	800	2.2	150	40
P3002Z_	140	180	280	360	4	5	800	2.2	150	40
P3602Z_	160	220	320	440	4	5	800	2.2	150	40
P4202Z_	190	250	380	500	4	5	800	2.2	150	30
P4802Z_	220	300	440	600	4	5	800	2.2	150	30
P6002Z_	275	350	550	700	4	5	800	2.2	150	30

\* For individual "ZA," "ZB," and "ZC" surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

• V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

V<sub>S</sub> is measured at 100 V/µs.

- Special voltage (V<sub>S</sub> and  $\dot{V}_{DRM}$ ) and holding current (I<sub>H</sub>) requirements are available upon request.

• Off-state capacitance is measured between Pins 4-3 and Pins 2-3 at 1 MHz with a 2 V bias and is a typical value for "ZA" product. "ZB" and "ZC" capacitance is approximately 2x higher.

• Device is designed to meet balance requirements of GTS 8700 and GR 974.

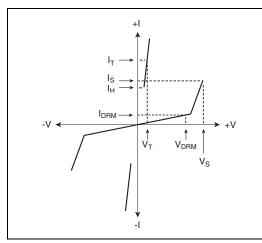
• Lower capacitance MC versions may be available. Contact factory for further information.

### Surge Ratings

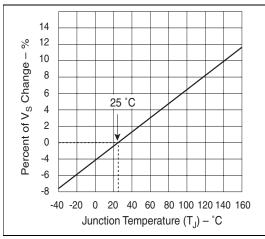
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

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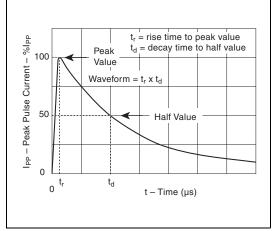
Package	Symbol	Parameter	Value	Unit
SIP	TJ	Operating Junction Temperature Range	-40 to +150	°C
	Ts	Storage Temperature Range	-65 to +150	°C
	$R_{\theta JA}$	Thermal Resistance: Junction to Ambient	90	°C/W

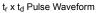


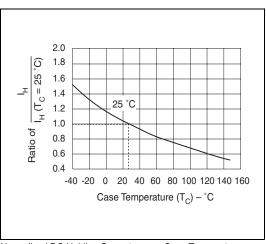
V-I Characteristics







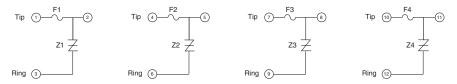




Normalized DC Holding Current versus Case Temperature

## **Four-Port Metallic Line Protector**

The four-port hybrid Single In-line Package (SIP) line protector protects multiple twisted pair from overcurrent and overvoltage conditions. Based on a SIP, it is equivalent to four discrete DO-214AA *SIDACtor* devices and four surface mount fuses. Available in surge current ratings up to 500 A, this four-port SIP line protector is ideal for densely populated line cards that cannot afford PCB inefficiencies or the use of series power resistors.



### Electrical Parameters

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	Co pF
P0080Z_	6	25	4	5	800	2.2	50	100
P0300Z_	25	40	4	5	800	2.2	50	110
P0640Z_	58	77	4	5	800	2.2	150	50
P0720Z_	65	88	4	5	800	2.2	150	50
P0900Z_	75	98	4	5	800	2.2	150	50
P1100Z_	90	130	4	5	800	2.2	150	40
P1300Z_	120	160	4	5	800	2.2	150	40
P1500Z_	140	180	4	5	800	2.2	150	40
P1800Z_	170	220	4	5	800	2.2	150	30
P2300Z_	190	260	4	5	800	2.2	150	30
P2600Z_	220	300	4	5	800	2.2	150	30
P3100Z_	275	350	4	5	800	2.2	150	30
P3500Z_	320	400	4	5	800	2.2	150	30

 $^{\ast}$  For individual "ZA," "ZB," and "ZC" surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

+  $V_S$  is measured at 100 V/µs.

Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value for "ZA" and "ZB" product. "ZC" capacitance is approximately 2x the listed value.

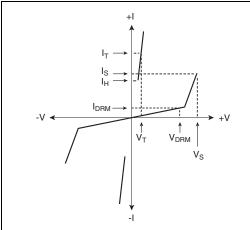
Lower capacitance MC versions may be available. Contact factory for further information.

### Surge Ratings

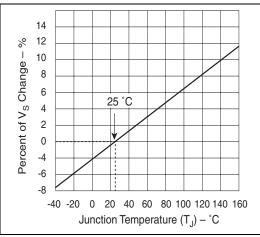
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
В	250	250	150	100	80	30	500
С	500	400	200	150	100	50	500

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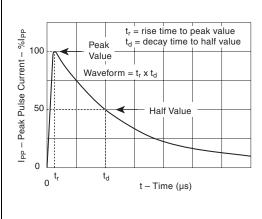
Package	Symbol	Parameter	Value	Unit
SIP	TJ	Operating Junction Temperature Range	-40 to +150	°C
	TS	Storage Temperature Range	-65 to +150	°C
	$R_{\theta JA}$	Thermal Resistance: Junction to Ambient	90	°C/W



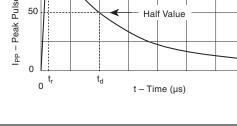


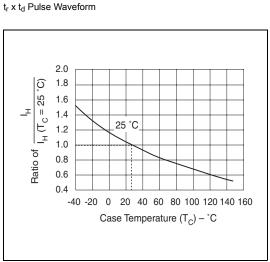












Normalized DC Holding Current versus Case Temperature

# **Fixed Voltage SLIC Protector**



These DO-214AA unidirectional protectors are constructed with a *SIDACtor* device and an integrated diode. They protect SLICs (Subscriber Line Interface Circuits) from damage during transient voltage activity and enable line cards to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA/ EIA-IS-968 (formerly known as FCC Part 68).



For specific design criteria, see details in Figure 3.21.

## Electrical Parameters

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	V <sub>F</sub> Volts	Ι <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	l <sub>T</sub> Amps	l <sub>H</sub> mAmps	C <sub>O</sub> pF
P0641S_	58	77	4	5	5	800	1	120	70
P0721S_	65	88	4	5	5	800	1	120	70
P0901S_	75	98	4	5	5	800	1	120	70
P1101S_	95	130	4	5	5	800	1	120	70

\* For individual "SA" and "SC" surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. I<sub>PP</sub> applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

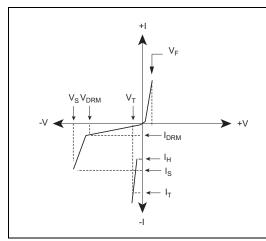
+  $V_{S}$  and  $V_{F}$  are measured at 100 V/µs.

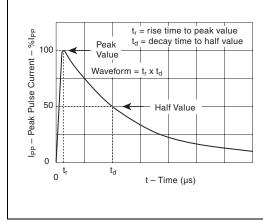
- Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.
- Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value for "SA" and "SB" product. "SC" capacitance is approximately 2x the listed value.
- Parallel capacitive loads may affect electrical parameters.

### Surge Ratings (Preliminary Data)

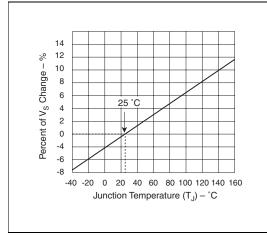
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	I <sub>PP</sub> 10x160 µs Amps	l <sub>PP</sub> 10x560 μs Amps	I <sub>PP</sub> 10x1000 µs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
С	500	400	200	120	100	50	500

Package	Symbol	Parameter	Value	Unit
DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
	TS	Storage Temperature Range	-65 to +150	°C
	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	90	°C/W



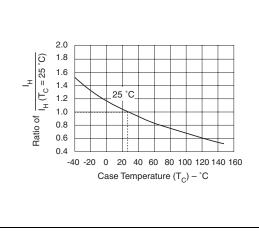


V-I Characteristics









Normalized DC Holding Current versus Case Temperature

# **Twin SLIC Protector**



Subscriber Line Interface Circuits (SLIC) are highly susceptible to transient voltages, such as lightning and power cross conditions. To minimize this threat, Teccor provides this dualchip, fixed-voltage SLIC protector device.

For specific design criteria, see details in Figure 3.23.

### Electrical Parameters

Part	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	VT	VF	I <sub>DRM</sub>	ls	Гт	Ін	Co
Number *	Pins 1	-2, 2-3	Pins	s 1-3	Volts	Volts	μAmps	mAmps	Amps	mAmps	pĔ
P0641CA2	58	77	58	77	4	5	5	800	1	120	60
P0721CA2	65	88	65	88	4	5	5	800	1	120	60
P0901CA2	75	98	75	98	4	5	5	800	1	120	60
P1101CA2	95	130	95	130	4	5	5	800	1	120	60

\* For surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. I<sub>PP</sub> applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

+  $V_S$  and  $V_F$  are measured at 100 V/µs.

- Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

Off-state capacitance is measured across pins 1-2 or 2-3 at 1 MHz with a 2 V bias. Capacitance across pins 1-3 is approximately half.

• Parallel capacitive loads may affect electrical parameters.

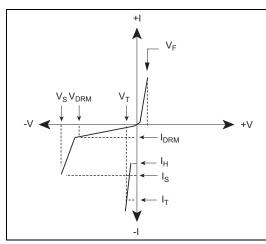
Compliance with GR 1089 or UL 60950 power cross tests may require special design considerations. Contact the factory for further information.

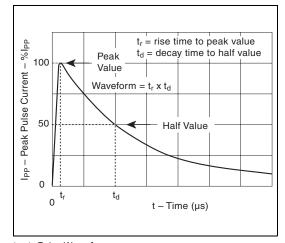
### Surge Ratings (Preliminary Data)

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
A	150	150	90	50	45	20	500

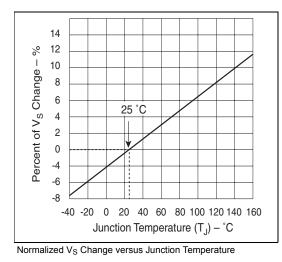
### Thermal Considerations

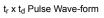
Package	Symbol	Parameter	Value	Unit
Modified DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
Pin 3	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
Pin 1 Pin 2	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	85	°C/W

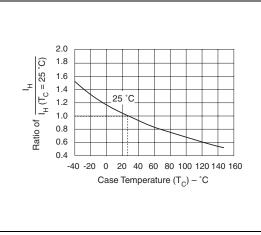




V-I Characteristics

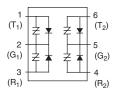






### Normalized DC Holding Current versus Case Temperature

# **Multiport SLIC Protector**



This multiport line protector is designed as a single-package solution for protecting multiple twisted pair from overvoltage conditions. Based on a six-pin SOIC package, it is equivalent to four discrete DO-214AA packages. Available in surge current ratings up to 500 A for a 2x10  $\mu$ s event, the multiport line protector is ideal for densely populated line cards that cannot afford PCB inefficiencies or the use of series power resistors.

For specific design criteria, see details in Figure 3.24.

### **Electrical Parameters**

	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts							
Part Number *	Pi 1-2, 4-5,	2-3,	Pi 1-3,	ns 4-6	V <sub>T</sub> Volts	V <sub>F</sub> Volts	I <sub>DRM</sub> μAmps	ls mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P0641U_	58	77	58	77	4	5	5	800	1	120	70
P0721U_	65	88	65	88	4	5	5	800	1	120	70
P0901U_	75	98	75	98	4	5	5	800	1	120	70
P1101U_	95	130	95	130	4	5	5	800	1	120	70

\* For individual "UA" and "UC" surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

+  $V_S$  and  $V_F$  are measured at 100 V/µs.

· Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

• Off-state capacitance is measured across pins 1-2, 2-3, 4-5, or 5-6 at 1 MHz with a 2 V bias and is a typical value. Capacitance across pins 1-3 or 4-6 is approximately half. "UC" capacitance is approximately 2x the listed value for "UA" product.

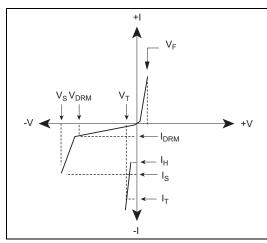
• Parallel capacitive loads may affect electrical parameters.

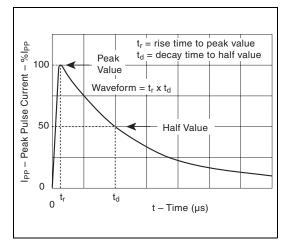
#### Surge Ratings

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	50	45	20	500
С	500	400	200	120	100	50	500

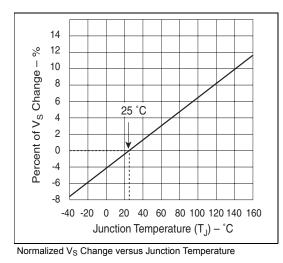
### Thermal Considerations

Package	Symbol	Parameter	Value	Unit
Modified MS-013	TJ	Operating Junction Temperature Range	-40 to +150	°C
6 5	TS	Storage Temperature Range	-65 to +150	°C
1 2 3 4 3 4	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W

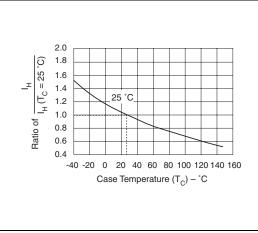




V-I Characteristics



t<sub>r</sub> x t<sub>d</sub> Pulse Wave-form

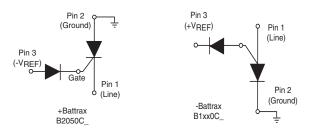


Normalized DC Holding Current versus Case Temperature

# **Battrax SLIC Protector**

This solid state protection device can be referenced to either a positive or negative voltage source. The B1xx0C\_ is for a -V<sub>REF</sub> and the B2050C\_ is for a +V<sub>REF</sub>. Designed using an SCR and a gate diode, the B1xx0C\_ *Battrax* begins to conduct at  $|-V_{REF}| + |-1.2 \text{ V}|$  while the B2050C\_ *Battrax* begins to conduct at  $|+V_{REF}| + |1.2 \text{ V}|$ .

For a diagram of a Battrax application, see Figure 3.29.



### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> µAmps	I <sub>GT</sub> mAmps	l <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
B1100C_	-V <sub>REF</sub>   +  -1.2 V	-V <sub>REF</sub>   +  -10 V	4	5	100	1	100	50
B1160C_	-V <sub>REF</sub>   +  -1.2 V	-V <sub>REF</sub>   +  -10 V	4	5	100	1	160	50
B1200C_	-V <sub>REF</sub>   +  -1.2 V	-V <sub>REF</sub>   +  -10 V	4	5	100	1	200	50
B2050C_	+V <sub>REF</sub>   +  1.2 V	+V <sub>REF</sub>   +  10 V	4	5	50	1	5	50

\* For individual "CA" and "CC" surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

•  $I_{PP}$  ratings assume  $V_{REF}$  = ±48 V.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

V<sub>S</sub> is measured at 100 V/µs.

• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value. "CC" product is approximately 2x the listed value.

Positive Battrax information is preliminary data.

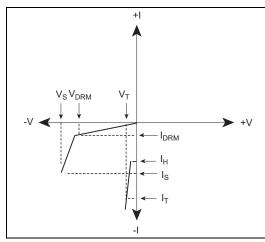
• V<sub>REF</sub> maximum value for the negative Battrax is -200 V.

• V<sub>REF</sub> maximum value for the positive Battrax is 110 V.

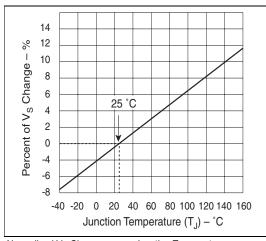
### Surge Ratings

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
А	150	150	90	60	50	40	500
С	500	400	200	150	100	50	500

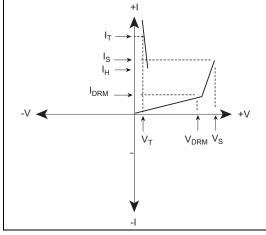
Package	Symbol	Parameter	Value	Unit
Modified DO-214AA	TJ	Operating Junction Temperature Range	-40 to +150	°C
Pin 3 (V <sub>BEF</sub> )	TS	Storage Temperature Range	-65 to +150	°C
Pin 1 (Line) Pin 2 (Ground)	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	85	°C/W

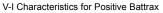


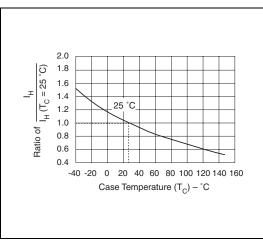
V-I Characteristics for Negative Battrax



Normalized V<sub>S</sub> Change versus Junction Temperature

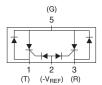






Normalized DC Holding Current versus Case Temperature

# **Battrax Dual Negative SLIC Protector**



This solid state *Battrax* protection device is referenced to a negative voltage source. Its dual-chip package also includes internal diodes for transient protection from positive surge events.

For a diagram of a Battrax application, see Figure 3.27.

### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	V <sub>F</sub> Volts	I <sub>DRM</sub> μAmps	I <sub>GT</sub> mAmps	l <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
B1101U_	-V <sub>REF</sub>   +  -1.2V	-V <sub>REF</sub>   +  -10V	4	5	5	100	1	100	50
B1161U_	-V <sub>REF</sub>   +  -1.2V	-V <sub>REF</sub>   +  -10V	4	5	5	100	1	160	50
B1201U_	-V <sub>REF</sub>   +  -1.2V	-V <sub>REF</sub>   +  -10V	4	5	5	100	1	200	50

\* For individual "UA" and "UC" surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

• IPP ratings assume a VREF = -48 V.

• V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

V<sub>S</sub> is measured at 100 V/µs.

• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value. "UC" product is approximately 2x the listed value.

• V<sub>REF</sub> maximum value for the B1101, B1161, and/or B1201 is -200 V.

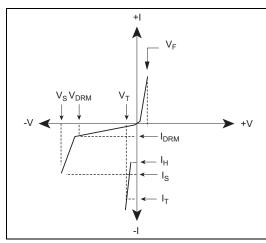
## Surge Ratings

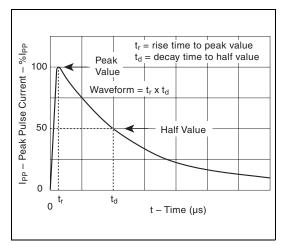
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	I <sub>PP</sub> 10x160 µs Amps	l <sub>PP</sub> 10x560 μs Amps	I <sub>PP</sub> 10x1000 µs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
Α	150	150	90	50	45	20	500
C**	500	400	200	120	100	50	500

\*\* Call factory for release date.

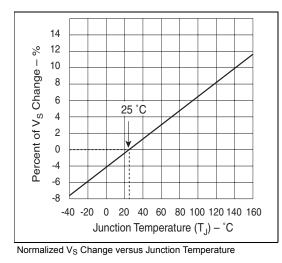
### Thermal Considerations

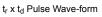
Package	Symbol	Parameter	Value	Unit
Modified MS-013	TJ	Operating Junction Temperature Range	-40 to +125	°C
6 5	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
1 2 3 4 4	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W

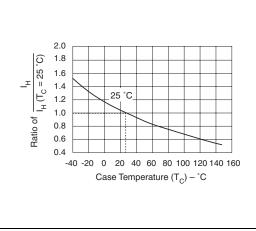




V-I Characteristics

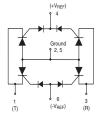






### Normalized DC Holding Current versus Case Temperature

## **Battrax Dual Positive/Negative SLIC Protector**



This Battrax device protects Subscriber Line Interface Circuits (SLIC) that use both a positive and negative Ring voltage. It limits transient voltages with rise times of 100 V/  $\mu s$  to  $V_{REF}$  ±10 V.

Teccor's six-pin *Battrax* devices are constructed using four SCRs and four gate diodes. The SCRs conduct when a voltage that is more negative than  $-V_{REF}$  (and/or more positive than  $+V_{REF}$ ) is applied to the cathode (Pins 1 and 3) of the SCR. During conduction, the SCRs appear as a low-resistive path which forces all transients to be shorted to ground.

For a diagram of a Battrax application, see Figure 3.30.

### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	Ι <sub>DRM</sub> μAmps	I <sub>GT</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	С <sub>О</sub> pF
B3104U_	-V <sub>REF</sub>   +  ±1.2V	-V <sub>REF</sub>   +  ±10V	4	5	100	1	100	50
B3164U_	-V <sub>REF</sub>   +  ±1.2V	-V <sub>REF</sub>   +  ±10V	4	5	100	1	160	50
B3204U_	-V <sub>REF</sub>   +  ±1.2V	-V <sub>REF</sub>   +  ±10V	4	5	100	1	200	50

\* For individual "UA" and "UC" surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

I<sub>PP</sub> ratings assume a V<sub>REF</sub> = ±48 V.

V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

V<sub>S</sub> is measured at 100 V/µs.

• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value. "UC" product is approximately 2x the listed value.

Positive Battrax information is preliminary data.

• V<sub>REF</sub> maximum value for the negative Battrax is -200 V.

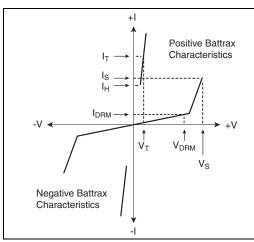
• V<sub>REF</sub> maximum value for the positive Battrax is 110 V.

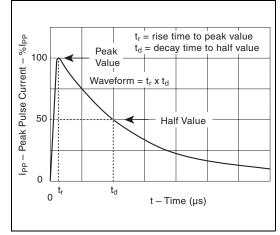
#### Surge Ratings

Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
Α	150	150	90	50	45	20	500
C**	500	400	200	120	100	50	500

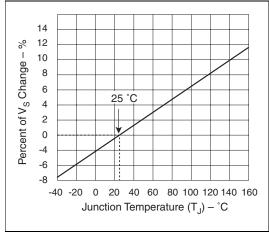
\*\* Call factory for release date.

Package	Symbol	Parameter	Value	Unit
Modified MS-013	TJ	Operating Junction Temperature Range	-40 to +125	°C
6	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
1 2 3 5 4 3 3 5 4	$R_{\theta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W

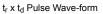


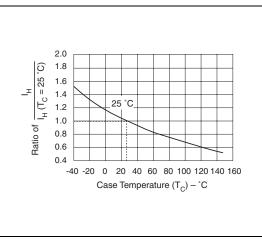






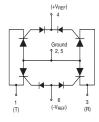






Normalized DC Holding Current versus Case Temperature

# **Battrax Quad Negative SLIC Protector**



This *Battrax* device is an integrated overvoltage protection solution for SLIC-based (Subscriber Line Interface Circuit) line cards. This six-pin device is constructed using four SCRs and four gate diodes.

The device is referenced to  $V_{BAT}$  and conducts when a voltage that is more negative than - $V_{REF}$  is applied to the cathode (pins 1, 3, 4, or 6) of the SCR. During conduction, all negative transients are shorted to Ground. All positive transients are passed to Ground by steering diodes.

For specific diagrams showing these Battrax applications, see Figure 3.28.

### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> µAmps	I <sub>GT</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
B1101U_4	-V <sub>REF</sub>   +  -1.2V	-V <sub>REF</sub>   +  -10V	4	5	100	1	100	50
B1161U_4	-V <sub>REF</sub>   +  -1.2V	-V <sub>REF</sub>   +  -10V	4	5	100	1	160	50
B1201U_4	-V <sub>REF</sub>   +  -1.2V	-V <sub>REF</sub>   +  -10V	4	5	100	1	200	50

\* For individual "UA" and "UC" surge ratings, see table below.

General Notes:

- All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.
- $I_{\mbox{\scriptsize PP}}$  is a repetitive surge rating and is guaranteed for the life of the product.

•  $I_{PP}$  ratings assume a  $V_{REF}$  = ±48 V.

V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

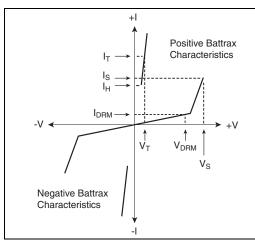
V<sub>S</sub> is measured at 100 V/µs.

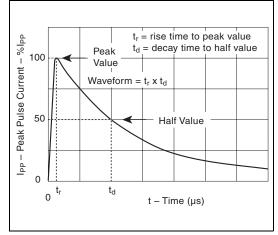
- Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value. "UC" product is approximately 2x the listed value.
- V<sub>REF</sub> maximum value for the negative Battrax is -200 V.

### Surge Ratings

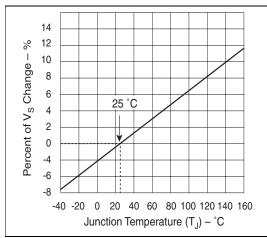
Series	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
Α	150	150	90	50	45	20	500
С	500	400	200	120	100	50	500

Package	Symbol	Parameter	Value	Unit
Modified MS-013	TJ	Operating Junction Temperature Range	-40 to +125	°C
6	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
1 2 3 5 4 3 3 5 4	$R_{ heta JA}$	Thermal Resistance: Junction to Ambient	60	°C/W



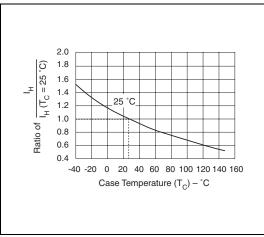


V-I Characteristics



Normalized V<sub>S</sub> Change versus Junction Temperature

t<sub>r</sub> x t<sub>d</sub> Pulse Wave-form



Normalized DC Holding Current versus Case Temperature

# **CATV and HFC SIDACtor Device**



This *SIDACtor* device is a 1000 A solid state protection device offered in a TO-220 package. It protects equipment located in the severe surge environment of Community Antenna TV (CATV) applications.

Used in Hybrid Fiber Coax (HFC) applications, this device replaces the gas tube traditionally used for station protection, because a *SIDACtor* device has a much tighter voltage tolerance.

### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	l <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	l <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF Pins 1-3
P1400AD	120	160	3	5	800	2.2	50	200
P1800AD	170	220	5.5	5	800	2.2	50	150

\* For surge ratings, see table below.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

• Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

• V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

V<sub>S</sub> is measured at 100 V/µs.

- Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

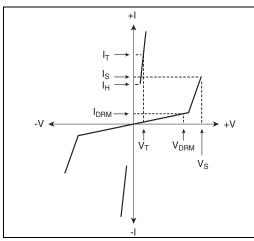
• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value.

### Surge Ratings

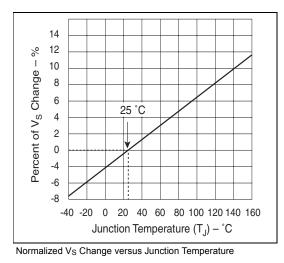
Series	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
D	1000	250	120	500

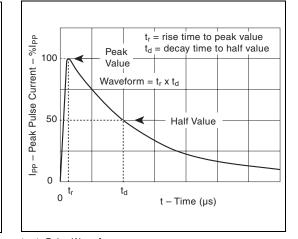
### **Thermal Considerations**

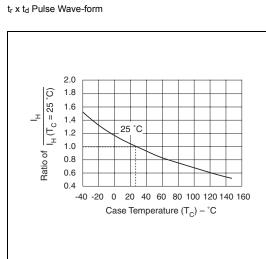
Package	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature Range	-40 to +150	°C
Modified TO-220	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
	$R_{0JA}$	Thermal Resistance: Junction to Ambient	60	°C/W



V-I Characteristics







Normalized DC Holding Current versus Case Temperature

# **High Surge Current SIDACtor Device**



This *SIDACtor* device is a 1000 A solid state protection device offered in a TO-220 package. It protects equipment located in the severe surge environment of Community Antenna TV (CATV) applications.

This device can replace the gas tubes traditionally used for station protection because *SIDACtor* devices have much tighter voltage tolerances.

### **Electrical Parameters**

Part	V <sub>DRM</sub>	Vs	VT	I <sub>DRM</sub>	ls	Ιτ	IH	C <sub>O</sub> pF
Number *	Volts	Volts	Volts	μAmps	mAmps	Amps	mAmps	Pins 1-3
P6002AD	550	700	5.5	5	800	2.2	50	60

\* For surge ratings, see table below.

## **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts		I <sub>S</sub>	I <sub>T</sub> Amps	I <sub>H</sub>	C <sub>O</sub> pF Pins 1-3
Number	VOILS	VOILS	VOILS	µAmps	mAmps	Amps	mAmps	FILIS 1-5
P3100AD	280	360	5.5	5	800	2.2	120	115

\* For surge ratings, see table below.

General Notes:

All measurements are made at an ambient temperature of 25 °C. I<sub>PP</sub> applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM.</sub>

V<sub>S</sub> is measured at 100 V/µs.

· Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value.

### Surge Ratings

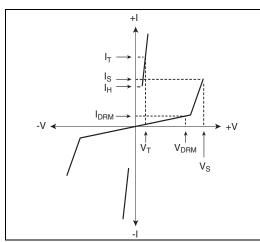
Series	l <sub>PP</sub> 8x20 μs Amps	l <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
D	1000	250	120	1000

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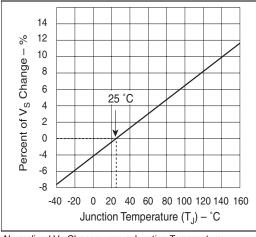
### Thermal Considerations

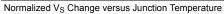
Package	Symbol	Parameter	Value	Unit
TJ		Operating Junction Temperature Range	-40 to +150	°C
Modified TO-220	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
PIN 1 PIN 2	R <sub>θJA</sub>	Thermal Resistance: Junction to Ambient	60	°C/W

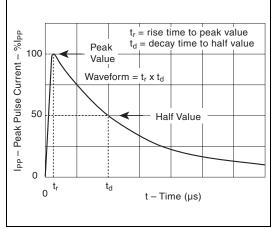
Note: P6002AD is shown. P3100AD has no center lead.

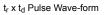


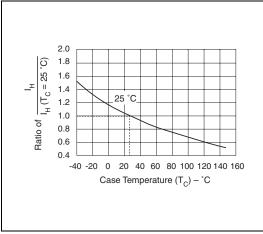
V-I Characteristics











Normalized DC Holding Current versus Case Temperature

**Data Sheets** 

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# CATV Line Amplifiers/Power Inserters SIDACtor Device



This *SIDACtor* device is a 5000 A solid state protection device offered in a non-isolated TO-218 package. It protects equipment located in the severe surge environment of CATV (Community Antenna TV) applications.

In CATV line amplifiers and power inserters, this device can replace the gas tubes traditionally used for station protection because *SIDACtor* devices have much tighter voltage tolerances.

### **Electrical Parameters**

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	Ι <sub>DRM</sub> μAmps	l <sub>S</sub> mAmps	I <sub>T</sub> Amps **	l <sub>H</sub> mAmps	C <sub>O</sub> pF
P1900ME	140	220	4	5	800	2.2/25	50	750
P2300ME	180	260	4	5	800	2.2/25	50	750

 $^{*}$  For surge ratings, see table below.  $^{**}$  I\_T is a free air rating; heat sink I\_T rating is 25 A.

General Notes:

• All measurements are made at an ambient temperature of 25 °C. IPP applies to -40 °C through +85 °C temperature range.

• IPP is a repetitive surge rating and is guaranteed for the life of the product.

· Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.

V<sub>DRM</sub> is measured at I<sub>DRM</sub>.

+  $V_S$  is measured at 100 V/µs.

• Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.

• Off-state capacitance is measured at 1 MHz with a 2 V bias and is a typical value.

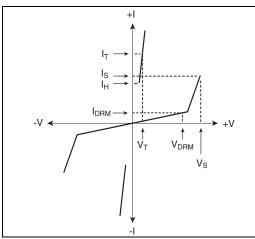
### Surge Ratings

Series	l <sub>PP</sub> 8x20 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/µs
E	5000	400	500

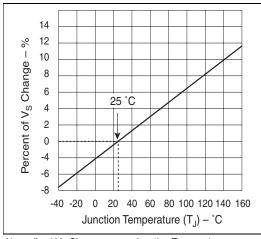
Package	Symbol	Parameter	Value	Unit
270	TJ	Operating Junction Temperature Range	-40 to +150	°C
TO-218	Τ <sub>S</sub>	Storage Temperature Range	-65 to +150	°C
	T <sub>C</sub>	Maximum Case Temperature	100	°C
	R <sub>θJC</sub> ∗	Thermal Resistance: Junction to Case	1.7	°C/W
	R <sub>0JA</sub>	Thermal Resistance: Junction to Ambient	56	°C/W
1 2 3 (No Connection	n)			

### **Thermal Considerations**

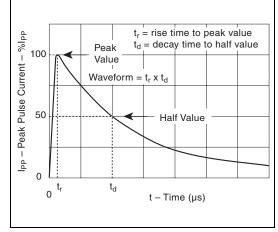
\* R<sub>0JC</sub> rating assumes the use of a heat sink and on state mode for extended time at 25 A, with average power dissipation of 29.125 W.

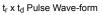


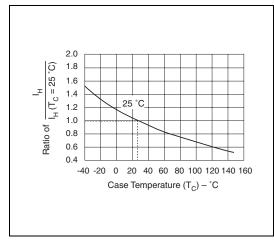
V-I Characteristics











Normalized DC Holding Current versus Case Temperature

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# **TeleLink Fuse**



The *TeleLink* Surface Mount (SM) surge resistant fuse offers circuit protection without requiring a series resistor. When used in conjunction with the *SIDACtor* Transient Voltage Suppressor (TVS), the *TeleLink* SM fuse and the *SIDACtor* TVS provide a complete regulatory-compliant solution for standards such as GR 1089, TIA/EIA-IS-968, UL 60950, and ITU K.20 and K.21 (formerly known as FCC Part 68). No series resistor is required for the F1250T and F1251T to comply with these standards.

Contact factory for enhanced K.20 and K.21 details.

### Surge Ratings

TeleLink SM Fuse	l <sub>PP</sub> 2x10 μs Amps	l <sub>PP</sub> 10x160 μs Amps	l <sub>PP</sub> 10x560 μs Amps	l <sub>PP</sub> 10x1000 μs Amps
F0500T	not rated	75	45	35
F1250T	500	160	115	100
F1251T	500	160	115	100

### **Interrupting Values**

			I <sup>2</sup> t Measured		Interrupting	Rating	
TeleLink SM Fuse	Voltage Rating	Current Rating	at DC Rated Voltage	Voltage, Current	MIN	TYP	МАХ
F0500T	250 V	500 mA	1.3 A <sup>2</sup> s	600 V, 40 A	1 s	2 s	60 s
F1250T	250 V	1.25 A	22.2 A <sup>2</sup> s	600 V, 60 A *	1 s	2 s	60 s
F1251T	250 V	2 A	30 A <sup>2</sup> s	600 V, 60 A *	1 s	2 s	60 s

\* Interrupt test characterized at 50° to 70° phase angle. Phase angles approximating 90° may result in damage to the body of the fuse. Notes:

• The *TeleLink* SM fuse is designed to carry 100% of its rated current for four hours and 250% of its rated current for one second minimum and 120 seconds maximum. Typical time is four to 10 seconds. For optimal performance, an operating current of 80% or less is recommended.

• I<sup>2</sup>t is a non-repetitive RMS surge current rating for a period of 16.7 ms.

### **Resistance Ratings**

	Typical Voltage Drop	DC Cold R	tesistance
TeleLink SM Fuse	@ Rated Current	MIN	MAX
F0500T	0.471 V	0.420 Ω	0.640 Ω
F1250T	0.205 V	0.107 Ω	0.150 Ω
F1251T	0.110 V	0.050 Ω	0.100 Ω

Notes:

- Typical inductance  $\cong$  4  $\mu H$  up to 500 MHz.

• Resistance changes 0.5% for every °C.

• Resistance is measured at 10% rated current.

## **Qualification Data**

The F1250T and F1251T meet the following test conditions per GR 1089 **without** additional series resistance. However, in-circuit test verification is required. Note that considerable heating may occur during Test 4 of the Second Level AC Power Fault Test.

### First Level Lightning Surge Test

Test	Surge Voltage Volts	Wave-form μs	Surge Current Amps	Repetitions Each Polarity
1	±600	10x1000	100	25
2	±1000	10x360	100	25
3	±1000	10x1000	100	25
4	±2500	2x10	500	10
5	±1000	10x360	25	5

### Second Level Lightning Surge Test

Test	Surge Voltage	Wave-form	Surge Current	Repetitions Each
	Volts	μs	Amps	Polarity
1	±5000	2x10	500	1

### **First Level AC Power Fault Test**

Test	Applied Voltage, 60 Hz V <sub>RMS</sub>	Short Circuit Current Amps	Duration	
1	50	0.33	15 min	
2	100	0.17	15 min	
3	200, 400, 600	1 at 600 V	60 applications, 1 s each	
4	1000	1	60 applications, 1 s each	
5	*	*	60 applications, 5 s each	
6	600	0.5	30 s each	
7	600	2.2	2 s each	
8	600	3	1 s each	
9	1000	5	0.5 s each	

\* Test 5 simulates a high impedance induction fault. For specific information, please contact Teccor Electronics.

### Second Level AC Power Fault Test for Non-Customer Premises Equipment

Test	Applied Voltage, 60 Hz V <sub>RMS</sub>	Short Circuit Current Amps	Duration
1	120, 277	30	30 min
2	600	60	5 s
3	600	7	5 s
4	100-600	2.2 at 600 V	30 min

Notes:

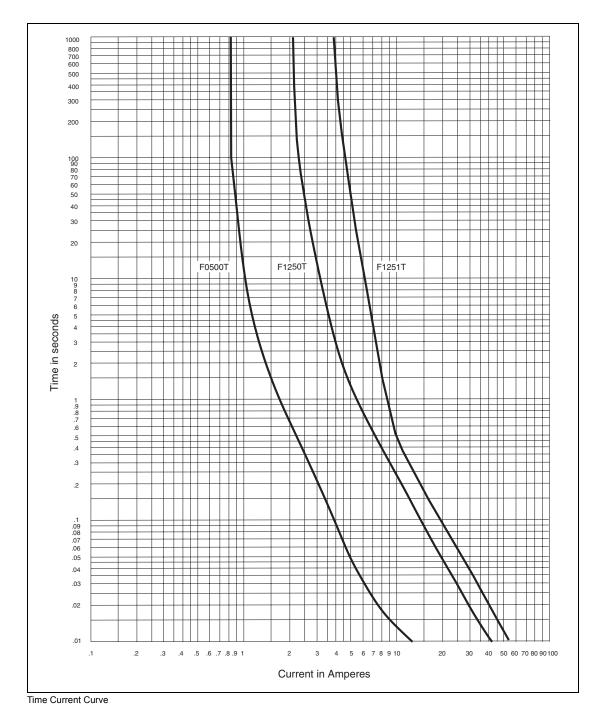
• Power fault tests equal or exceed the requirements of UL 60950 3rd edition.

• Test 4 is intended to produce a maximum heating effect. Temperature readings can exceed 150 °C.

Test 2 may be dependent on the closing angle of the voltage source. Fuse is characterized at 50° to 70°. Closing angles approximating 90° may result in damage to the body of the fuse.

Use caution when routing internal traces adjacent to the F1250T and F1251T.





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## **Temperature Derating Curve**

Operating temperature is -55 °C to +125 °C with proper correction factor applied.

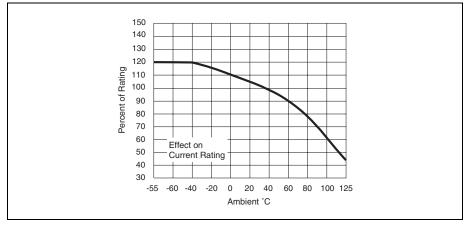


Chart of Correction Factor

### Maximum Temperature Rise

TeleLink Fuse	Temperature Reading	
F0500T	≤75 °C (167 °F) *	
F1250T	≤75 °C (167 °F) *	
F1251T	≤75 °C (167 °F) *	

 $^{\ast}$  Higher currents and PCB layout designs can affect this parameter.

Notes:

• Readings are measured at rated current after temperature stabilizes

The F1250T meets the requirements of UL 248-14. However, board layout, board trace widths, and ambient temperature values can cause higher than expected rises in temperature. During UL testing, the typical recorded heat rise for the F1250T at 2.2 A was 120 °C.

### Package Symbolization

Marking	F0500T	F1250T	F1251T	Manufactured in USA	Manufactured in Taiwan
FU	F			U	
FT	F				Т
JU		J		U	
JT		J			Т
NU			Ν	U	
NT			Ν		Т

TeleLink Fuse